# Medium Power Transistor (32V, 2A) 2SD1766/2SD1758/2SD1862/2SD1189F/ 2SD1055/2SD1919/2SD1227M

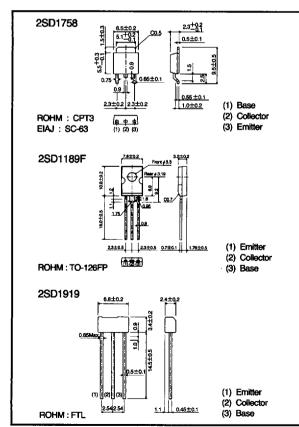
#### Features

1) Low  $V_{CE(set)}$ .  $V_{CE(set)} = 0.16V (Typ.)$ (Ic/I<sub>B</sub> = 2A/0.2A)

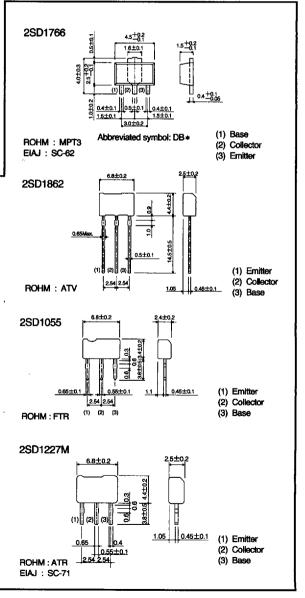
Complements the
 2SB1188/2SB1182/2SB1240/2SB
 891F/2SB822/2SB1277/2SB911M

#### Structure

Epitaxial planar type NPN silicon transistor



External dimensions (Units: mm)



\*Denotes hre

**■ 7828999 0016907 265**  ■

(96-217-B24

# ●Absolute maximum ratings (Ta = 25℃)

Parameter		Symbol	Limits	Unit	
Collector-base voltage		Vcвo	40	V	
Collector-em	nitter voltage	VCEO	32	V	
Emitter-base	voltage	VEBO	5	V	
		lc lc	. 2 A(		
Collector cui	Collector current		2.5	A(Pulse) *1	
	0001700		0.5	10/	
	2SD1766		2	W *2	
Collector	2SD1758		10	W (Tc=25℃)	
power	2SD1862,2SD1227M	Pc	1	w *3	
dissipation	0004400E		1.2	VV	
	2SD1189F		5	W (Tc=25℃)	
	2SD1055,2SD1919		0.75	W	
Junction temperature		Tj	150	ဗ	
Storage tem	Storage temperature		<b>−55~150</b>	င	

<sup>\*1</sup> Single pulse Pw=20ms

### ●Electrical characteristics (Ta = 25°C)

Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage		ВУсво	40	_		٧	lc=50 μ A
Collector-emitt	er breakdown voltage	BVCEO	32	_	_	٧	lc=1mA
Emitter-base b	reakdown voltage	BVEBO	5	_	_	٧	le=50 μ A
Collector cutof	f current	Ісво	_	_	1	μΑ	V <sub>CB</sub> =20V
Emitter cutoff current		IEBO	_	_	1	μΑ	V <sub>EB</sub> =4V
	2SD1766,2SD1758, 2SD1189F		82	_	390		
DC current	2SD1862	hre	120	-	390		Vc==3V lc=0.5A *
transfer ratio	2SD1055	1112	180		390	_	Vc=3V, lc=0.5A *
	2SD1919,2SD1227M		120	_	270		
Collector-emitter saturation voltage		VCE(sat)	_	0.5	0.8	٧	Ic/I <sub>B</sub> =2A/0.2A *
Transition frequency		fī	_	100	-	MHz	V <sub>CE</sub> =5V, I <sub>E</sub> =-50mA, f=100MHz *
Output capacitance		Cob	_	30		pF	VCB=10V, IE=0A, f=1MHz

<sup>\*</sup> Measured using pulse current.

<sup>\*2</sup> On 40 x 40 x 0.7 mm ceramic board.

<sup>\*3</sup> Printed circuit board: 1.7 mm thick, collector copper plating 1 cm² or more.

#### ●Packaging specifications and hre

·	Package		Taping			Bulk		
		Symbol	T100	TL	TV2	_	_	TL2
Туре	hfe	Basic ordering unit (pieces)	1000	2500	2500	1000	2000	2500
2SD1766	PQR		0	_			_	_
2SD1758	PQR		_	0	_	_	_	_
2SD1862	QR			_	0		_	_
2SD1189F	PQR			_	_	0	_	<del>-</del>
2SD1055	R		_			_	0	_
2SD1919	Q		_	_		_		0
2SD1227M	Q		T -	_	_	_	0	_

#### hre values are classified as follows:

Item	Р	Q	R
hfE	82~180	120~270	180~390

#### Electrical characteristic curves

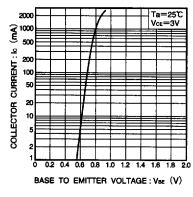


Fig.1 Grounded emitter propagation characteristics

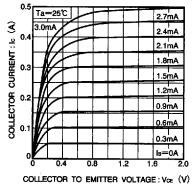


Fig.2 Grounded emitter output characteristics

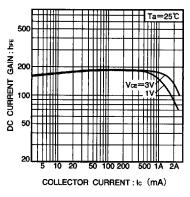


Fig.3 DC current gain vs. collector current

7828999 0016909 038

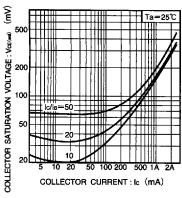


Fig.4 Collector-emitter saturation voltage vs. collector current

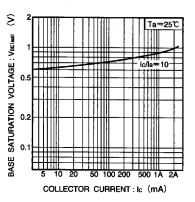


Fig.5 Collector-emitter saturation voltage vs. collector current

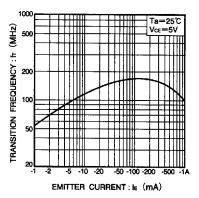
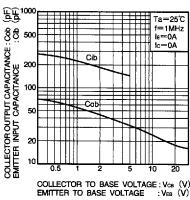


Fig.6 Transition frequency vs. emitter current



ig.7 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

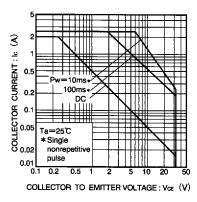


Fig.8 Safe operating area (2SD1766)

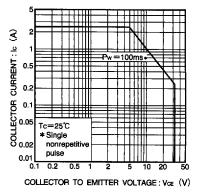


Fig.9 Safe operating area (2SD1758)

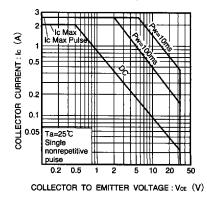


Fig.10 Safe operating area (2SD1862, 2SD1227M)

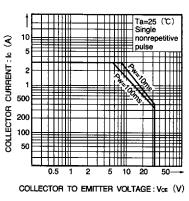


Fig.11 Safe operating area (2SD1189F)

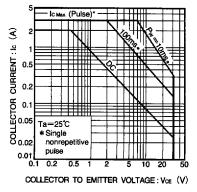
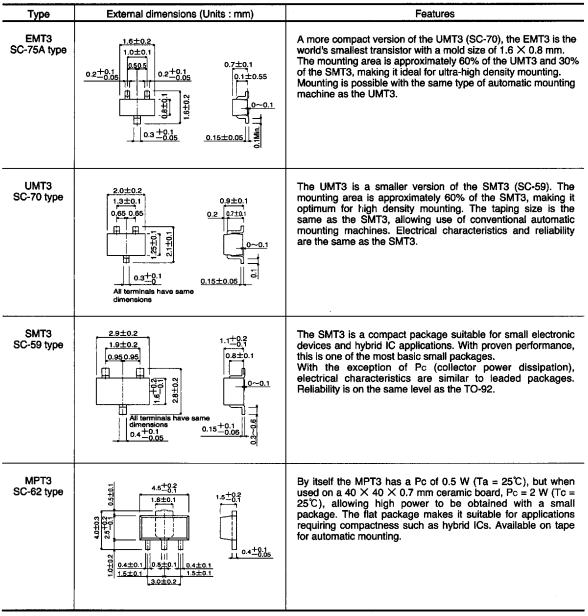


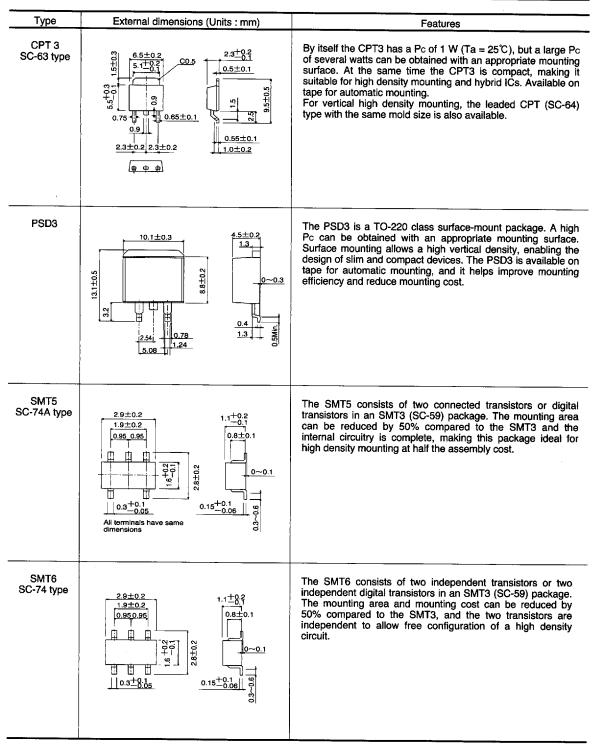
Fig.12 Safe operating area (2SD1055, 2SD1919)

# **Packages**

ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.

Types and features of surface-mount packages

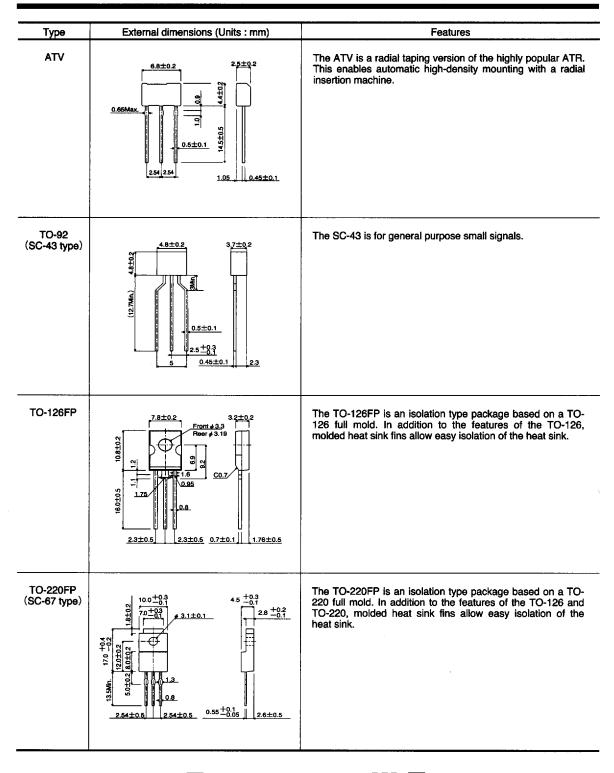




Туре	External dimensions (Units : mm)	Features
UMT5 SC-88A type	2.0±0.2 1,3±0.1 0,85 0,85 0,7 0,005 All terminals have same dimensions	The UMT5 consists of two connected transistors or digital transistors in a UMT3 (SC-70) package. The mounting area can be reduced by 50% compared to the UMT3 and the internal circuitry is completed, making this package ideal for high density mounting at half the assembly cost.
UMT6 SC-88 type	2.0±0.2 1,3±0.1 0.65 0.65 0.7 0.7 0.7 0.7 0.7 0.7 0.7 0.7	The UMT6 consists of two independent transistors or two independent digital transistors in a UMT (SC-70) package. The mounting area and mounting cost can be reduced by 50% compared to the UMT3, and the two transistors are independent to allow free configuration of a high density circuit.

# ●Types and features of leaded packages

Туре	External dimensions (Units : mm)	Features
SPT (SC-72 type)	2±0,2 0.45±0.15 0.45±0.15 0.5 0.45±0.15 0.5 0.45±0.15	The SPT is a smaller version of the conventional TO-92 type. The body size (3×4×2 mm³) has been reduced to 1/4 that of the TO-92 (5×5×4 mm³). The SPT is available on tape for automatic insertion, and less space is occupied on the printed circuit board than the TO-92. Reliability is the same as the TO-92.
FTR	0.65±0.1 2.4±0.2 0.55±0.1 0.55±0.1 0.45±0.1 0.45±0.1	SIL type with a height of 3.4 mm and a lead pitch of 2.54 mm.
FTL	0.65Max 2.4±0.2 0.65Max 2.4±0.2 0.5±0.1 0.5±0.1	The FTL is a radial taping version of the highly popular FTR. This enables automatic high-density mounting with a radial insertion machine.
ATR (SC-71 type)	0.65Max	SC-71type with a height of 4.4 mm and a Pc=1W type.



Type	External dimensions (Units : mm)	Features
TO-220FN	\$3.2±0.2	The TO-220FN features the same performance as the TO-220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short-circuiting problems with neighboring components and the chassis.  To make the height to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP.